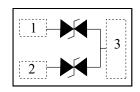


# PESDNC3FD5VB

# **Bi-directional 5V Normal Capacitance ESD Protector**

#### Description

The PESDNC3FD5VB protects sensitive semiconductor components from damage or upset due to electrostatic discharge (ESD) and other voltage induced transient events. They feature large cross-sectional area junctions for conducting high transient currents, offer desirable electrical characteristics for board level protection, such as fast response time, low operating voltage. It gives designer the flexibility to protect one bi-directional line in applications where arrays are not practical.



Top View

#### Feature

- 100W peak pulse power per line (t<sub>P</sub> = 8/20µs)
- DFN1006-3L package
- Bidirectional configurations
- Response time is typically < 1ns</p>
- Low clamping voltage
- Transient protection for data lines to IEC61000-4-2(ESD) ±30KV(air), ±30KV(contact); IEC61000-4-4 (EFT) 40A (5/50ns)

## Applications

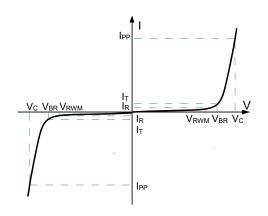
- Cell phone
- PMP
- > MID
- PDA
- Digital camera
- Other electronics equipments

#### **Mechanical Characteristics**

- Lead finish:100% matte Sn(Tin)
- Mounting position: Any
- Qualified max reflow temperature:260°C
- Device meets MSL 1 requirements
- Pure tin plating: 7 ~ 17 um
- ➢ Pin flatness:≤3mil

#### **Electronics Parameter**

Symbol	Parameter		
VRWM	Peak Reverse Working Voltage		
IR	Reverse Leakage Current @ VRWM		
V <sub>BR</sub>	Breakdown Voltage @ I⊤		
Ιτ	Test Current		
IPP	Maximum Reverse Peak Pulse Current		
Vc	Clamping Voltage @ IPP		
P <sub>PP</sub>	Peak Pulse Power		
CJ	Junction Capacitance		
IF	Forward Current		
VF	Forward Voltage @ I <sub>F</sub>		



## Electrical characteristics per line@25 $^{\circ}$ (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Peak Reverse Working Voltage	V <sub>RWM</sub>				5	V
Breakdown Voltage	V <sub>BR</sub>	lt = 1mA	5.6	6.2	7.0	V
Reverse Leakage Current	IR	V <sub>RWM</sub> = 5V T=25°C			1.0	μA
Clamping Voltage	Vc	I <sub>PP</sub> =1A			7	V
Clamping Voltage	Vc	I <sub>PP</sub> =3A			8	V
Clamping Voltage	Vc	I <sub>PP</sub> =5A			9	V
Junction Capacitance	Cj	V <sub>R</sub> =0V f = 1MHz	12.5	16.5	21	pF

### Absolute maximum rating@25℃

Rating	Symbol	Value	Units
Peak Pulse Power (t <sub>p</sub> =8/20µs)	P <sub>pp</sub>	100	W
Operating Temperature	TJ	-55 to 150	°C
Storage Temperature	Tstg	-55 to 150	°C

### **Typical Characteristics**

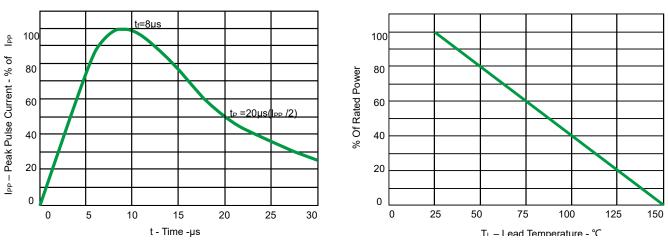


Fig 1.Pulse Waveform

Fig 2.Power Derating Curve

#### 22 f=1MHz 21 C-Junction capacitance (pF) 19 17 15 13 11 -5 -4 -3 -2 -1 0 2 3 4 5 1 V<sub>R</sub>- Reverse voltage (V)

Fig 3. Capacitance vs. Reveres voltage

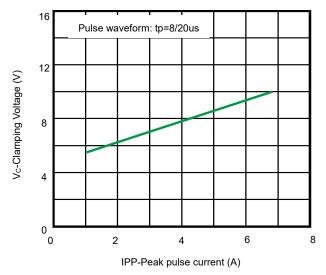
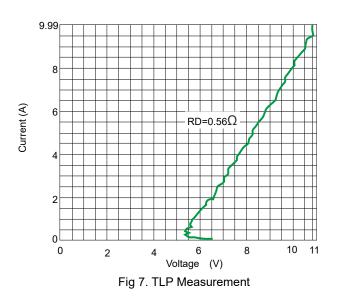


Fig 5. Clamping voltage vs. Peak pulse current



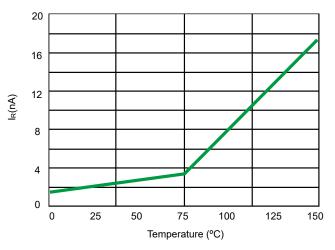


Fig 4.Typical Leakage Current vs. Temperature

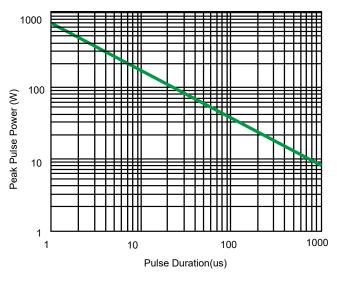
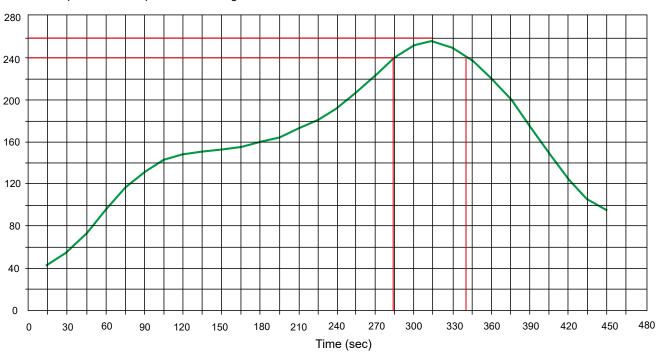


Fig 6. Non-Repetitive Peak Pulse Power vs. Pulse time

# PESDNC3FD5VB

### PESDNC3FD5VB

#### **Solder Reflow Recommendation**



Peak Temp=257°C, Ramp Rate=0.802deg. °C/sec

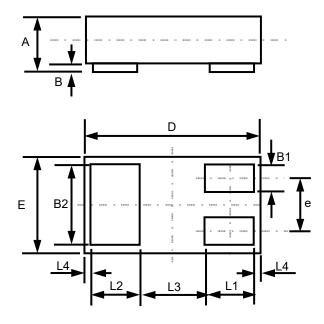
### **PCB** Design

For TVS diodes a low-ohmic and low-inductive path to chassis earth is absolutely mandatory in order to achieve good ESD protection. Novices in the area of ESD protection should take following suggestions to heart:

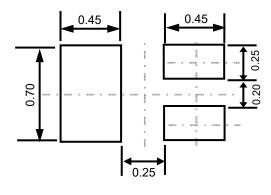
- > Do not use stubs, but place the cathode of the TVS diode directly on the signal trace.
- > Do not make false economies and save copper for the ground connection.
- > Place via holes to ground as close as possible to the anode of the TVS diode.
- Use as many via holes as possible for the ground connection.
- > Keep the length of via holes in mind! The longer the more inductance they will have.

### PESDNC3FD5VB

# Product dimension (DFN1006-3L)



Dim	Millimeters			
Dim	MIN	Тур	МАХ	
А	0.33	0.47	0.498	
В	0.00	0.03	0.05	
B1	0.10	0.15	0.20	
B2	0.45	0.50	0.55	
D	0.85	1.00	1.15	
Е	0.45	0.60	0.75	
е		0.35		
L1	0.20	0.25	0.30	
L2	0.20	0.25	0.30	
L3		0.39		
L4		0.05		

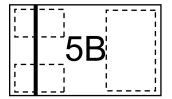


Suggested PCB Layout

Unit:mm

### PESDNC3FD5VB

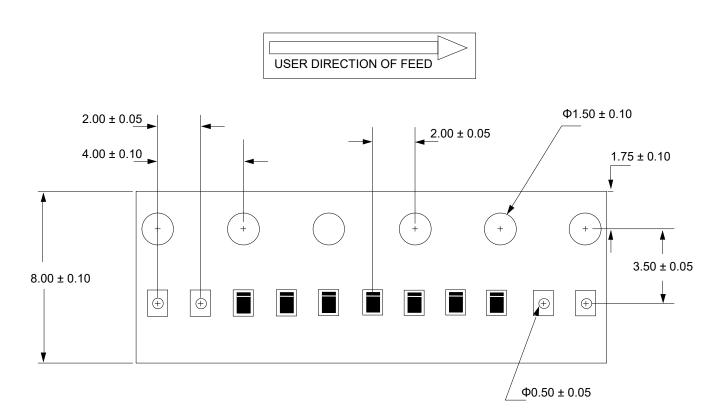
# Marking information



# **Ordering information**

Device	Package	Reel	Shipping
PESDNC3FD5VB	DFN1006-3L (Pb-Free)	7"	10000 / Tape & Reel

## Load with information



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